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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	147
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pe1500-pqg208i

SRAM and FIFO

ProASIC3E devices have embedded SRAM blocks along their north and south sides. Each variable-aspect-ratio SRAM block is 4,608 bits in size. Available memory configurations are 256×18, 512×9, 1k×4, 2k×2, and 4k×1 bits. The individual blocks have independent read and write ports that can be configured with different bit widths on each port. For example, data can be sent through a 4-bit port and read as a single bitstream. The embedded SRAM blocks can be initialized via the device JTAG port (ROM emulation mode) using the UJTAG macro.

In addition, every SRAM block has an embedded FIFO control unit. The control unit allows the SRAM block to be configured as a synchronous FIFO without using additional core VersaTiles. The FIFO width and depth are programmable. The FIFO also features programmable Almost Empty (AEMPTY) and Almost Full (AFULL) flags in addition to the normal Empty and Full flags. The embedded FIFO control unit contains the counters necessary for generation of the read and write address pointers. The embedded SRAM/FIFO blocks can be cascaded to create larger configurations.

PLL and CCC

ProASIC3E devices provide designers with very flexible clock conditioning capabilities. Each member of the ProASIC3E family contains six CCCs, each with an integrated PLL.

The six CCC blocks are located at the four corners and the centers of the east and west sides.

To maximize user I/Os, only the center east and west PLLs are available in devices using the PQ208 package. However, all six CCC blocks are still usable; the four corner CCCs allow simple clock delay operations as well as clock spine access.

The inputs of the six CCC blocks are accessible from the FPGA core or from one of several inputs located near the CCC that have dedicated connections to the CCC block.

The CCC block has these key features:

- Wide input frequency range (f_{IN_CCC}) = 1.5 MHz to 350 MHz
- Output frequency range (f_{OUT_CCC}) = 0.75 MHz to 350 MHz
- Clock delay adjustment via programmable and fixed delays from –7.56 ns to +11.12 ns
- 2 programmable delay types for clock skew minimization
- Clock frequency synthesis

Additional CCC specifications:

- Internal phase shift = 0°, 90°, 180°, and 270°. Output phase shift depends on the output divider configuration.
- Output duty cycle = 50% ± 1.5% or better
- Low output jitter: worst case < 2.5% × clock period peak-to-peak period jitter when single global network used
- Maximum acquisition time = 300 µs
- Low power consumption of 5 mW
- Exceptional tolerance to input period jitter— allowable input jitter is up to 1.5 ns
- Four precise phases; maximum misalignment between adjacent phases of 40 ps × (350 MHz / f_{OUT_CCC})

Global Clocking

ProASIC3E devices have extensive support for multiple clocking domains. In addition to the CCC and PLL support described above, there is a comprehensive global clock distribution network.

Each VersaTile input and output port has access to nine VersaNets: six chip (main) and three quadrant global networks. The VersaNets can be driven by the CCC or directly accessed from the core via multiplexers (MUXes). The VersaNets can be used to distribute low-skew clock signals or for rapid distribution of high fanout nets.

Table 2-4 • Overshoot and Undershoot Limits [1]

VCCI and VMV	Average VCCI–GND Overshoot or Undershoot Duration as a Percentage of Clock Cycle [2]	Maximum Overshoot/ Undershoot [2]
2.7 V or less	10%	1.4 V
	5%	1.49 V
3 V	10%	1.1 V
	5%	1.19 V
3.3 V	10%	0.79 V
	5%	0.88 V
3.6 V	10%	0.45 V
	5%	0.54 V

Notes:

1. Based on reliability requirements at 85°C.
2. The duration is allowed at one out of six clock cycles. If the overshoot/undershoot occurs at one out of two cycles, the maximum overshoot/undershoot has to be reduced by 0.15 V.
3. This table does not provide PCI overshoot/undershoot limits.

I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every ProASIC®3E device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges. In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in Figure 2-1 on page 2-4.

There are five regions to consider during power-up.

ProASIC3E I/Os are activated only if ALL of the following three conditions are met:

1. VCC and VCCI are above the minimum specified trip points (Figure 2-1 on page 2-4).
2. VCCI > VCC – 0.75 V (typical)
3. Chip is in the operating mode.

VCCI Trip Point:
Ramping up: 0.6 V < trip_point_up < 1.2 V
Ramping down: 0.5 V < trip_point_down < 1.1 V

VCC Trip Point:
Ramping up: 0.6 V < trip_point_up < 1.1 V
Ramping down: 0.5 V < trip_point_down < 1 V

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

Table 2-17 • Summary of I/O Timing Character istics—Software Default Settings
–2 Speed Grade, Commercial-Case Conditions: T J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 3.0 V

I/O Standard	Drive Strength (mA)	Equivalent Software Default Drive Strength Option) [1]	Slew Rate	Capacitive Load (pF)	External Resistor (:)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{PYS} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)
3.3 V LVTTL / 3.3 V LVCMOS	12	12	High	35	–	0.49	2.74	0.03	0.90	1.17	0.32	2.79	2.14	2.45	2.70	4.46	3.81
3.3 V LVCMOS Wide Range[2]	100 µA	12	High	35	–	0.49	4.24	0.03	1.36	1.78	0.32	4.24	3.25	3.78	4.17	6.77	5.79
2.5 V LVCMOS	12	12	High	35	–	0.49	2.80	0.03	1.13	1.24	0.32	2.85	2.61	2.51	2.61	4.52	4.28
1.8 V LVCMOS	12	12	High	35	–	0.49	2.83	0.03	1.08	1.42	0.32	2.89	2.31	2.79	3.16	4.56	3.98
1.5 V LVCMOS	12	12	High	35	–	0.49	3.30	0.03	1.27	1.60	0.32	3.36	2.70	2.96	3.27	5.03	4.37
3.3 V PCI	Per PCI spec	–	High	10	25 [3]	0.49	2.09	0.03	0.78	1.17	0.32	2.13	1.49	2.45	2.70	3.80	3.16
3.3 V PCI-X	Per PCI-X spec	–	High	10	25[3]	0.49	2.09	0.03	0.78	1.17	0.32	2.13	1.49	2.45	2.70	3.80	3.16
3.3 V GTL	20 [4]	–	High	10	25	0.45	1.55	0.03	2.19	–	0.32	1.52	1.55	–	–	3.19	3.22
2.5 V GTL	20 [4]	–	High	10	25	0.45	1.59	0.03	1.83	–	0.32	1.61	1.59	–	–	3.28	3.26
3.3 V GTL+	35	–	High	10	25	0.45	1.53	0.03	1.19	–	0.32	1.56	1.53	–	–	3.23	3.20
2.5 V GTL+	33	–	High	10	25	0.45	1.65	0.03	1.13	–	0.32	1.68	1.57	–	–	3.35	3.24
HSTL (I)	8	–	High	20	50	0.49	2.37	0.03	1.59	–	0.32	2.42	2.35	–	–	4.09	4.02
HSTL (II)	15 [4]	–	High	20	25	0.49	2.26	0.03	1.59	–	0.32	2.30	2.03	–	–	3.97	3.70
SSTL2 (I)	15	–	High	30	50	0.49	1.59	0.03	1.00	–	0.32	1.62	1.38	–	–	3.29	3.05
SSTL2 (II)	18	–	High	30	25	0.49	1.62	0.03	1.00	–	0.32	1.65	1.32	–	–	3.32	2.99
SSTL3 (I)	14	–	High	30	50	0.49	1.72	0.03	0.93	–	0.32	1.75	1.37	–	–	3.42	3.04
SSTL3 (II)	21	–	High	30	25	0.49	1.54	0.03	0.93	–	0.32	1.57	1.25	–	–	3.24	2.92
LVDS/B-LVDS/ M-LVDS	24	–	High	–	–	0.49	1.40	0.03	1.36	–	–	–	–	–	–	–	–
LVPECL	24	–	High	–	–	0.49	1.36	0.03	1.22	–	–	–	–	–	–	–	–

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3V wide range as specified in the JESD8b specification.
3. Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-11 on page 2-38 for connectivity. This resistor is not required during normal operation.
4. Output drive strength is below JEDEC specification.
5. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5.

Table 2-19 • I/O Output Buffer Maximum Resistances [1] (continued)

Standard	Drive Strength	$R_{PULL\text{-}DOWN}$ (:)[2]	$R_{PULL\text{-}UP}$ (:)[3]
3.3 V GTL+	35 mA	12	–
2.5 V GTL+	33 mA	15	–
HSTL (I)	8 mA	50	50
HSTL (II)	15 mA [4]	25	25
SSTL2 (I)	15 mA	27	31
SSTL2 (II)	18 mA	13	15
SSTL3 (I)	14 mA	44	69
SSTL3 (II)	21 mA	18	32

Notes:

1. These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the Microsemi SoC Products Group website at www.microsemi.com/index.php?option=com_content&id=1671&lang=en&view=article.
2. $R_{(PULL\text{-}DOWN\text{-}MAX)}$ = (VOLspec) / IOLspec
3. $R_{(PULL\text{-}UP\text{-}MAX)}$ = (VCCImax – VOHspec) / IOHspec
4. Output drive strength is below JEDEC specification.

Table 2-20 • I/O Weak Pull-Up/Pull-Down Resistances
Minimum and Maximum Weak Pull-U p/Pull-Down Resistance Values

	$R_{(WEAK\ PULL\text{-}UP)}$ [1] (:)		$R_{(WEAK\ PULL\text{-}DOWN)}$ [2] (:)	
VCCI	Min.	Max.	Min.	Max.
3.3 V	10 k	45 k	10 k	45 k
3.3 V (Wide Range I/Os)	10 k	45 k	10 k	45 k
2.5 V	11 k	55 k	12 k	74 k
1.8 V	18 k	70 k	17 k	110 k
1.5 V	19 k	90 k	19 k	140 k

Notes:

1. $R_{(WEAK\ PULL\text{-}UP\text{-}MAX)}$ = (VCCImax – VOHspec) / $I_{(WEAK\ PULL\text{-}UP\text{-}MIN)}$
2. $R_{(WEAK\ PULL\text{-}DOWN\text{-}MAX)}$ = (VOLspec) / $I_{(WEAK\ PULL\text{-}DOWN\text{-}MIN)}$

Table 2-22 • Duration of Short Circuit Even t Before Failure (continued)

Temperature	Time before Failure
85°C	2 years
100°C	6 months

Table 2-23 • Schmitt Trigger Input Hysteresis
Hysteresis Voltage Value (typ.) for Schmitt Mode Input Buffers

Input Buffer Configuration	Hysteresis Value (typ.)
3.3 V LVTTL/LVCMOS/PCI/PCI-X (Schmitt trigger mode)	240 mV
2.5 V LVCMOS (Schmitt trigger mode)	140 mV
1.8 V LVCMOS (Schmitt trigger mode)	80 mV
1.5 V LVCMOS (Schmitt trigger mode)	60 mV

Table 2-24 • I/O Input Rise Time, Fall Time, and Related I/O Reliability*

Input Buffer	Input Rise/Fall Time (min.)	Input Rise/Fall Time (max.)	Reliability
LVTTL/LVCMOS (Schmitt trigger disabled)	No requirement	10 ns *	20 years (110°C)
LVTTL/LVCMOS (Schmitt trigger enabled)	No requirement	No requirement, but input noise voltage cannot exceed Schmitt hysteresis.	20 years (110°C)
HSTL/SSTL/GTL	No requirement	10 ns *	10 years (100°C)
LVDS/B-LVDS/M-LVDS/ LVPECL	No requirement	10 ns *	10 years (100°C)

Note: *For clock signals and similar edge-generating signals, refer to the "ProASIC3/E SSO and Pin Placement Guidelines" chapter of the ProASIC3E FPGA Fabric User's Guide. The maximum input rise/fall time is related to the noise induced into the input buffer trace. If the noise is low, then the rise time and fall time of input buffers can be increased beyond the maximum value. The longer the rise/fall times, the more susceptible the input signal is to the board noise. Microsemi recommends signal integrity evaluation/characterization of the system to ensure that there is no excessive noise coupling into input signals.

Timing Characteristics

Table 2-31 • 3.3 V LVCMOS Wide Range High Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V

Drive Strength	Equivalent Software Default Drive Strength Option [1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	4 mA	Std.	0.66	12.19	0.04	1.83	2.38	0.43	12.19	10.17	4.16	4.00	15.58	13.57	ns
		–1	0.56	10.37	0.04	1.55	2.02	0.36	10.37	8.66	3.54	3.41	13.26	11.54	ns
		–2	0.49	9.10	0.03	1.36	1.78	0.32	9.10	7.60	3.11	2.99	11.64	10.13	ns
100 µA	8 mA	Std.	0.66	7.85	0.04	1.83	2.38	0.43	7.85	6.29	4.71	4.97	11.24	9.68	ns
		–1	0.56	6.68	0.04	1.55	2.02	0.36	6.68	5.35	4.01	4.22	9.57	8.24	ns
		–2	0.49	5.86	0.03	1.36	1.78	0.32	5.86	4.70	3.52	3.71	8.40	7.23	ns
100 µA	12 mA	Std.	0.66	5.67	0.04	1.83	2.38	0.43	5.67	4.36	5.06	5.59	9.07	7.75	ns
		–1	0.56	4.82	0.04	1.55	2.02	0.36	4.82	3.71	4.31	4.75	7.71	6.59	ns
		–2	0.49	4.24	0.03	1.36	1.78	0.32	4.24	3.25	3.78	4.17	6.77	5.79	ns
100 µA	16 mA	Std.	0.66	5.35	0.04	1.83	2.38	0.43	5.35	3.96	5.15	5.76	8.75	7.35	ns
		–1	0.56	4.55	0.04	1.55	2.02	0.36	4.55	3.36	4.38	4.90	7.44	6.25	ns
		–2	0.49	4.00	0.03	1.36	1.78	0.32	4.00	2.95	3.85	4.30	6.53	5.49	ns
100 µA	24 mA	Std.	0.66	4.96	0.04	1.83	2.38	0.43	4.96	3.27	5.23	6.38	8.35	6.67	ns
		–1	0.56	4.22	0.04	1.55	2.02	0.36	4.22	2.78	4.45	5.43	7.11	5.67	ns
		–2	0.49	3.70	0.03	1.36	1.78	0.32	3.70	2.44	3.91	4.76	6.24	4.98	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. Software default selection highlighted in gray.
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Table 2-40 • 1.8 V LVCMOS Low Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	15.84	0.04	1.45	1.91	0.43	15.65	15.84	2.78	1.58	17.89	18.07	ns
	–1	0.56	13.47	0.04	1.23	1.62	0.36	13.31	13.47	2.37	1.35	15.22	15.37	ns
	–2	0.49	11.83	0.03	1.08	1.42	0.32	11.69	11.83	2.08	1.18	13.36	13.50	ns
4 mA	Std.	0.66	11.39	0.04	1.45	1.91	0.43	11.60	10.76	3.26	2.77	13.84	12.99	ns
	–1	0.56	9.69	0.04	1.23	1.62	0.36	9.87	9.15	2.77	2.36	11.77	11.05	ns
	–2	0.49	8.51	0.03	1.08	1.42	0.32	8.66	8.03	2.43	2.07	10.33	9.70	ns
6 mA	Std.	0.66	8.97	0.04	1.45	1.91	0.43	9.14	8.10	3.57	3.36	11.37	10.33	ns
	–1	0.56	7.63	0.04	1.23	1.62	0.36	7.77	6.89	3.04	2.86	9.67	8.79	ns
	–2	0.49	6.70	0.03	1.08	1.42	0.32	6.82	6.05	2.66	2.51	8.49	7.72	ns
8 mA	Std.	0.66	8.35	0.04	1.45	1.91	0.43	8.50	7.59	3.64	3.52	10.74	9.82	ns
	–1	0.56	7.10	0.04	1.23	1.62	0.36	7.23	6.45	3.10	3.00	9.14	8.35	ns
	–2	0.49	6.24	0.03	1.08	1.42	0.32	6.35	5.66	2.72	2.63	8.02	7.33	ns
12 mA	Std.	0.66	7.94	0.04	1.45	1.91	0.43	8.09	7.56	3.74	4.11	10.32	9.80	ns
	–1	0.56	6.75	0.04	1.23	1.62	0.36	6.88	6.43	3.18	3.49	8.78	8.33	ns
	–2	0.49	5.93	0.03	1.08	1.42	0.32	6.04	5.65	2.79	3.07	7.71	7.32	ns
16 mA	Std.	0.66	7.94	0.04	1.45	1.91	0.43	8.09	7.56	3.74	4.11	10.32	9.80	ns
	–1	0.56	6.75	0.04	1.23	1.62	0.36	6.88	6.43	3.18	3.49	8.78	8.33	ns
	–2	0.49	5.93	0.03	1.08	1.42	0.32	6.04	5.65	2.79	3.07	7.71	7.32	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

1.5 V LVCMOS (JESD8-11)

Low-Voltage CMOS for 1.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.5 V applications. It uses a 1.5 V input buffer and a push-pull output buffer.

Table 2-41 • Minimum and Maximum DC Input and Output Levels

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL [1]	IIH [2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA [3]	Max. mA [3]	µA [4]	µA [4]
2 mA	–0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2	16	13	10	10
4 mA	–0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	4	4	33	25	10	10
6 mA	–0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	6	6	39	32	10	10
8 mA	–0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	8	8	55	66	10	10
12 mA	–0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	12	12	55	66	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V< VIN < VIL.
2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

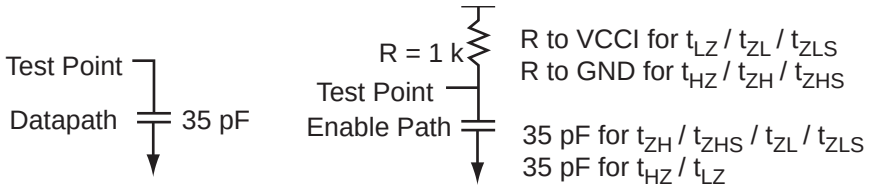

Figure 2-10 • AC Loading

Table 2-42 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C LOAD (pF)
0	1.5	0.75	–	35

Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.

3.3 V GTL+

Gunning Transceiver Logic Plus is a high-speed bus standard (JESD8-3). It provides a differential amplifier input buffer and an open-drain output buffer. The VCCI pin should be connected to 3.3 V.

Table 2-54 • Minimum and Maximum DC Input and Output Levels

3.3 V GTL+	VIL		VIH		VOL	VOH	IOL	OH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
35 mA	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.6	–	35	35	181	268	10	10

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
2. Currents are measured at 85°C junction temperature.

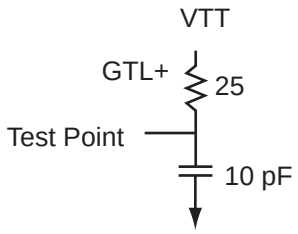

Figure 2-14 • AC Loading

Table 2-55 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.1	VREF + 0.1	1.0	1.0	1.5	10

Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.

Timing Characteristics

Table 2-56 • 3.3 V GTL+
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 3.0 V, VREF = 1.0 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.60	2.06	0.04	1.59	0.43	2.09	2.06			4.33	4.29	ns
–1	0.51	1.75	0.04	1.35	0.36	1.78	1.75			3.68	3.65	ns
–2	0.45	1.53	0.03	1.19	0.32	1.56	1.53			3.23	3.20	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.